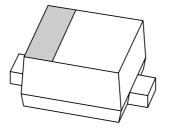
DISCRETE SEMICONDUCTORS

DATA SHEET



PMEG2005EBLow V_F MEGA Schottky barrier diode

Product data sheet Supersedes data of 2003 Feb 20 2003 Apr 04



Low V_F MEGA Schottky barrier diode

PMEG2005EB

FEATURES

Forward current: 0.5 AReverse voltage: 20 V

Very low forward voltage

· Guard ring protected

• Ultra small SMD package.

APPLICATIONS

• Ultra high-speed switching

· Voltage clamping

· Protection circuits

· Low current rectification

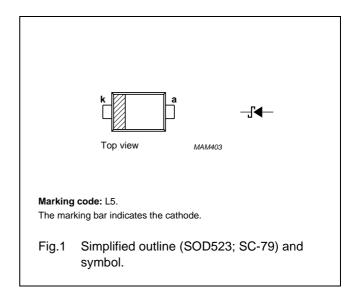
Low power consumption applications (e.g. handheld devices).

DESCRIPTION

Planar Maximum Efficiency General Application (MEGA) Schottky barrier diode, encapsulated in a SOD523 (SC-79) ultra small SMD plastic package.

PINNING

PIN	DESCRIPTION	
1	cathode	
2	anode	



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_R	continuous reverse voltage		_	20	V
I _F	continuous forward current		_	500	mA
I _{FRM}	repetitive peak forward current	t_p = 1 ms; $\delta \le 0.25$	_	3.5	Α
I _{FSM}	non-repetitive peak forward current	t = 8 ms square wave	_	6	Α
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	125	°C
T _{amb}	operating ambient temperature		-65	+125	°C

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ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V _F	continuous forward voltage	see Fig.2			
		I _F = 0.1 mA	120	180	mV
		I _F = 1 mA	180	240	mV
		I _F = 10 mA	245	290	mV
		I _F = 100 mA	320	380	mV
		I _F = 500 mA	430	480	mV
I _R	continuous reverse current	V _R = 10 V; see Fig.3; note 1	7	30	μΑ
C _d	diode capacitance	$V_R = 1 V$; $f = 1 MHz$; see Fig.4	24	30	pF

Note

1. Pulsed test: t_p = 300 μ s; δ = 0.02.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to	note 1	400	K/W
	ambient			

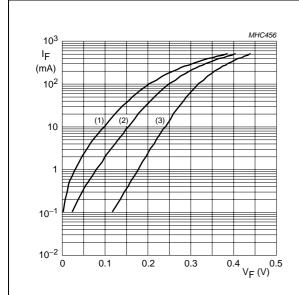
Note

1. Refer to SOD523 (SC-79) standard mounting conditions.

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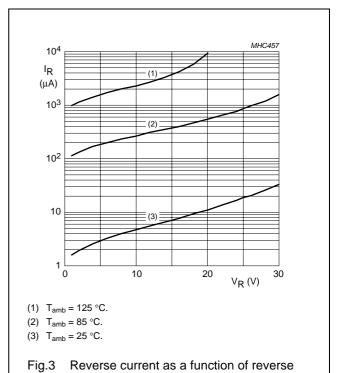
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GRAPHICAL DATA



- (1) $T_{amb} = 125 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.2 Forward current as a function of forward voltage; typical values.



voltage; typical values.

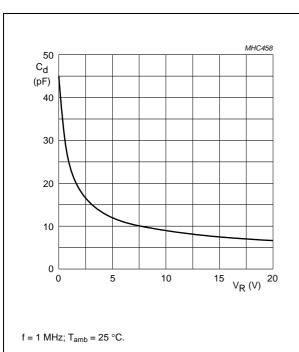


Fig.4 Diode capacitance as a function of reverse voltage; typical values.

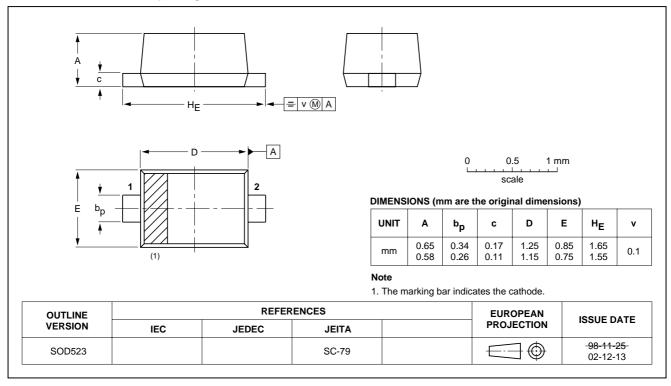
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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD523



Low V_F MEGA Schottky barrier diode

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- The product status of device(s) described in this document may have changed since this document was published
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